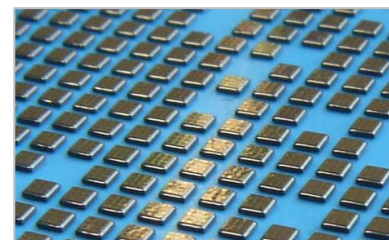




ELC-1550-27

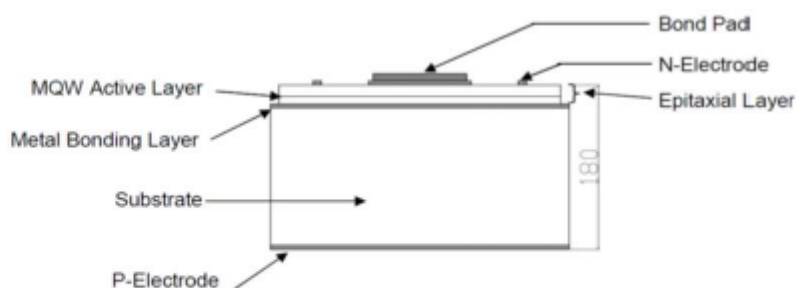
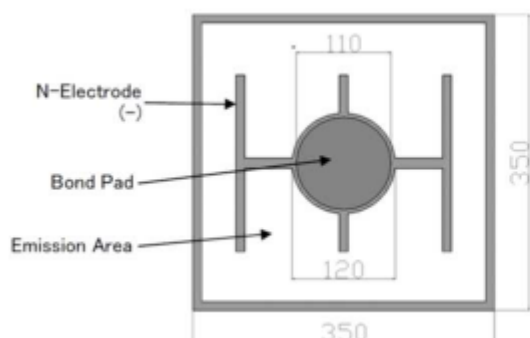
- Infrared LED bare chip die
- 1550 nm
- InGaAs MQW
- n-side up
- RoHS compliant



Electro-Optical Characteristics (T_{CASE} = 25°C)

Parameter	Condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak Wavelength	I _F =20 mA	λ _p		1550		nm
Output Power (bare die on TO-18 header)	I _F =20 mA	P _O		2.1		mW
Forward Voltage	I _F =20 mA	V _F		0.9		V

Outline Dimensions



All dimensions in μm

Die size	typ. 0.350 x 0.350 mm (14 mil)
Die thickness	typ. 0.180 mm (7 mil)
Bond pad size	Ø 0.110 mm
Contact metallization	gold alloy